



Semiconductor Materials Information

High k and ALD/CVD Metal Precursors

A Semiconductor Materials Report

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TABLE OF CONTENTS

	PAGE #
REPORT HIGHLIGHTS	5
Memory Capacitors.....	5
Back End of Line	7
Market Environment	8
1 INTRODUCTION	9
2 GATE DIELECTRICS	12
2.1 Application Description and Current Gate Materials	12
2.2 FUSI	15
2.2.1 Advantages of FUSI	17
2.2.2 FUSI Challenges.....	18
2.3 High- κ Dielectric and Metal-Gate Technology	18
2.4 Advantages of Metal Gate (vs. Polysilicon Gate)	19
2.4.1 Metal-Gate Challenges	19
High- κ Metal-Gate Process Flow Notes:.....	22
2.5 Future Gate Dielectrics and Requirements.....	24
2.6 Material Candidates and Precursors	26
2.7 Market Timing, Pricing, and Forecast.....	28
3 HIGH-K CAPACITORS FOR MEMORY DEVICES.....	29
3.1 Application Description.....	31
3.2 Current Capacitor materials.....	32
3.3 Future Dielectric Requirements.....	32
3.4 Materials Candidates and Precursors.....	33
3.5 Market Timing, Pricing, and Forecast.....	34
4 INTERCONNECT.....	36
4.1 Interconnect Trends	36
4.2 ALD Possible Interconnect Technology Applications	46
4.3 Metal Filled Contact Plugs	48
4.4 Alternative Interconnect Metals	51
4.4.1 Chemical Vapor Deposited Aluminum	52
4.5 Alternative Barrier, Seed, and Capping Metals.....	52
4.5.1 Barrier Metals for Copper.....	52
4.5.1 Copper Cap after CMP	54
4.6 Atomic Layer Deposition	55
4.7 Pricing, Timing, and Forecast	57
5 PRECURSOR DELIVERY	58
6 ORGANOMETALLIC PRECURSOR MARKET DYNAMICS.....	59
6.1 Supply Value Chain.....	60
6.2 Market Shares	62

6.2.1	Regional Supplier Ranking.....	62
6.2.2	Worldwide Market Shares.....	63
7	SUPPLIER PROFILES.....	64
7.1	Adeka.....	64
7.2	Air Liquide.....	64
7.3	Air Products & Chemicals (AP).....	65
7.4	SAFC (EpiChem/Sigma Aldrich).....	71
7.5	Dow Chemical (was Rohm and Haas) Electronic Materials.....	67
7.6	JSR Corporation and Tri Chemical Laboratories Inc.....	68
7.7	Linde.....	69
7.8	Praxair.....	70
7.9	UP Chemicals.....	71

List of Figures

Figure 1:	High- κ and ALD Applications.....	11
Figure 2:	DRAM Trench Capacitor Application.....	11
Figure 3:	DRAM Vertical Stacked Capacitor Application.....	12
Figure 4:	Current MOS Gate Structure.....	14
Figure 5:	Device with High- κ Gate Dielectric.....	14
Figure 6:	Device with Gate-First.....	15
Figure 7:	Device with Replacement-Metal Gate-Last.....	15
Figure 8:	SEM of FUSI Device.....	16
Figure 9:	FUSI Process Flow.....	16
Figure 10:	One Possible Metal-Gate-First Process Flow.....	21
Figure 11:	Intel Penryn's Replacement-Metal-Gate Process.....	23
Figure 12:	High- κ Gate Dielectric & Electrode Precursor Forecast.....	29
Figure 13:	70nm Stacked Capacitor.....	30
Figure 14:	High- κ Capacitor & Metal Electrode Precursors.....	35
Figure 15:	Chemical Structure of the Complexes TDMAT and TDEAT.....	50
Figure 16:	Revenue Forecast for WF ₆ Only at 90nm through 22nm.....	50
Figure 17:	Revenue Forecast for TDMAT only at 90nm through 22nm nodes.....	51
Figure 18:	Revenue Forecast for CVD/ALD Interconnect Metal Barriers, 2 Possible Scenarios.....	53
Figure 19:	CVD/ALD High- κ Materials Market for \leq 90nm, assumes Co as Barrier for \leq 22nm.....	59

Figure 20: CVD/ALD High- κ Materials Market for $\leq 90\text{nm}$, assumes Ru is Barrier for $\leq 22\text{nm}$	60
Figure 21: 2009 Worldwide Market Share Estimates for High- κ Precursors (includes Ti, Ta & Al precursors).....	63

List of Tables

Table 1: Front End Dielectric Materials & Processes, 2009 & 2012.....	6
Table 2: Interconnect Materials & Processes, 2009, 2013 and 2016.....	7
Table 3: Gate Related Sections of International Technology Roadmap for Semiconductors	26
Table 4: Dielectric Materials Capacitance.....	27
Table 5: ITRS DRAM Stacked Capacitor Technology Requirements—Near-term.....	32
Table 6: 2008 update of the 2007 ITRS for MPU Interconnect Technology Requirements	39
Table 7: 2008 update of 2007 ITRS DRAM Interconnect Technology Requirements	42
Table 8: 2007 ITRS, Interconnect Difficult Challenges	43
Table 9: Materials & Process Options for 2013 (32 nm) & 2016 (22 nm).....	44
Table 10: Organometallic Precursors: Synthesizers and Suppliers to the IC Market.....	61